



DATA SHEET

MOS INTEGRATED CIRCUIT μ PD3573

2 048-BIT CCD LINEAR IMAGE SENSOR

The μ PD3573 is a 2 048-bit linear image sensor consisting of charge coupled devices (CCDs), which converts light to voltage. This product is made up of a 2 048-bit photosensor array, charge transfer register with a pair of 1 024-bit CCDs, and sample and hold circuit. The photosensor has a 14 μ m pitch.

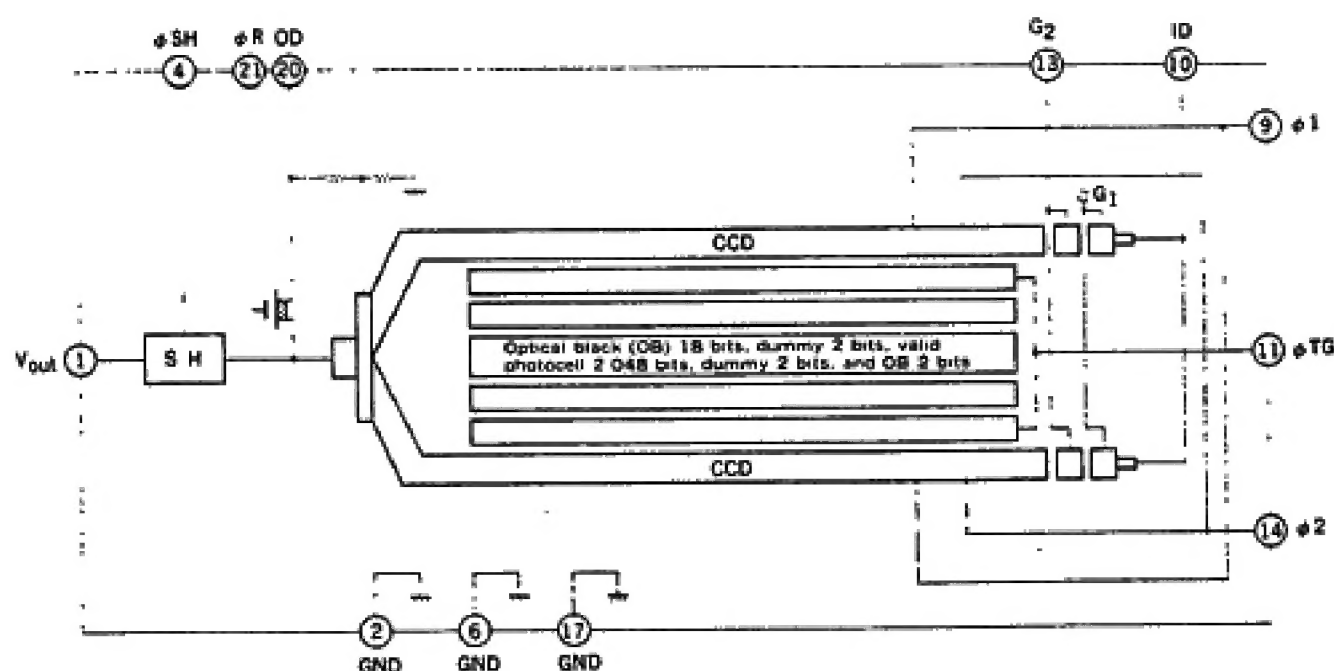
FEATURES

- Incorporates a sample and hold circuit.
- High response sensitivity: Providing a response ten times better than the existing equivalent NEC product (μ PD799D) to the light from a white fluorescent lamp
- Peak response wavelength: 550 nm green
- Reads the shorter side of a B4-size sheet at a resolution of 8 dot/mm
- Driven by a 12 V single power supply

ORDERING INFORMATION

Part Number	Package
μ PD3573D	22-pin ceramic DIP (CERDIP) (400 mil)

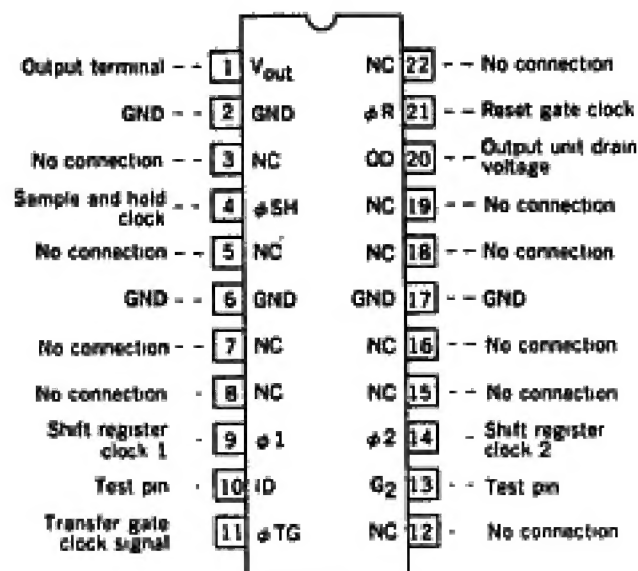
BLOCK DIAGRAM



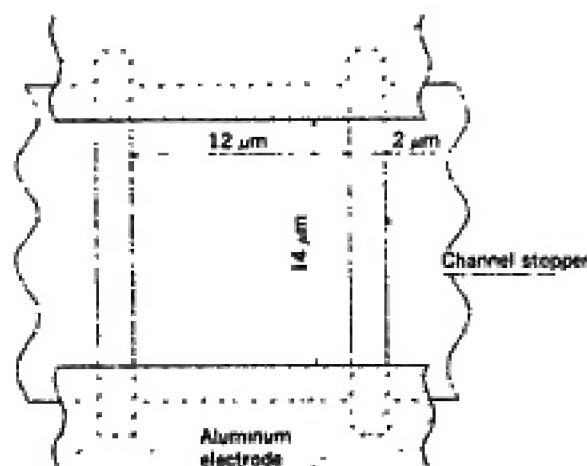
NEC cannot assume any responsibility for any circuits shown or represent that they are free from patent infringement.

T-41-55

PIN CONNECTION DIAGRAM (Top View)



PHOTOELEMENT STRUCTURE DIAGRAM

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

Output unit drain voltage	V_{OD}	-0.3 to +15	V
Test pin ID voltage	V_{ID}	-0.3 to +15	V
Shift register clock signal voltage	$V_{\phi 1}$	-0.3 to +15	V
	$V_{\phi 2}$	-0.3 to +15	V
Reset signal voltage	$V_{\phi R}$	-0.3 to +15	V
Transfer gate signal voltage	$V_{\phi TG}$	-0.3 to +15	V
Sample and hold signal voltage	$V_{\phi SH}$	-0.3 to +15	V
Operating ambient temperature	T_{opt}	-25 to +60	$^\circ C$
Storage temperature	T_{stg}	-40 to +100	$^\circ C$

T-41-55

RECOMMENDED OPERATING CONDITIONS ($T_a = -25$ to $+60^\circ\text{C}$)

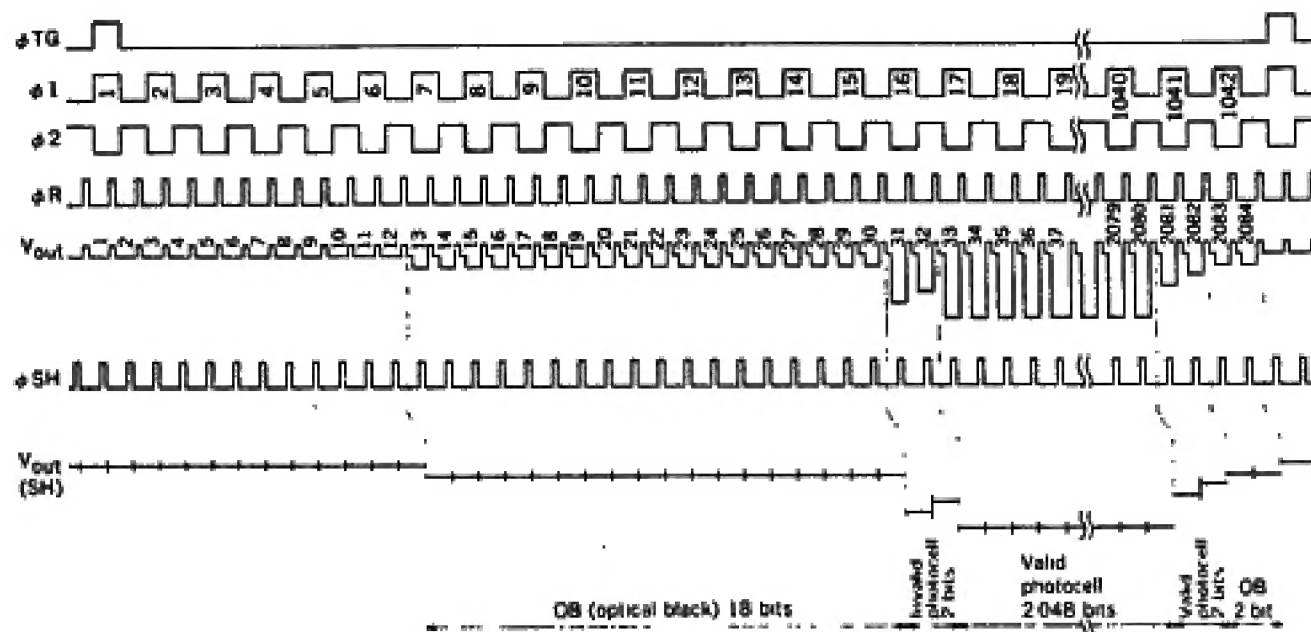
ITEM	SYMBOL	MIN.	TYP.	MAX.	UNIT
Output unit drain voltage	V_{OD}	11.4	12.0	12.6	V
Test pin G_2 voltage	V_{G2}		0		V
Test pin ID voltage	V_{ID}		12.0		V
Shift register clock 1 signal high level	$V_{\phi 1H}$	4.5	5.0	12.6	V
Shift register clock 1 signal low level	$V_{\phi 1L}$	-0.3	0	0.5	V
Shift register clock 2 signal high level	$V_{\phi 2H}$	4.5	5.0	12.6	V
Shift register clock 2 signal low level	$V_{\phi 2L}$	-0.3	0	0.5	V
Reset signal RH high level	$V_{\phi RH}$	8.0	12.0	12.6	V
Reset signal RL low level	$V_{\phi RL}$	-0.3	0	1.0	V
Transfer gate signal high level	$V_{\phi TGH}$	4.5	5.0	12.6	V
Transfer gate signal low level	$V_{\phi TGL}$	-0.3	0	0.5	V
Sample and hold signal high level	$V_{\phi SHH}$	8.0	12.0	12.6	V
Sample and hold signal low level	$V_{\phi SHL}$	-0.3	0	1.0	V
Data rate	$f_{\phi R}$		1	3	MHz

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$, $V_{OD} = 12.0\text{ V}$, $f_{\phi 1} = 1\text{ MHz}$, data rate = 2 MHz, storage time = 10 ms, light source: 2 856 K tungsten bulb.)

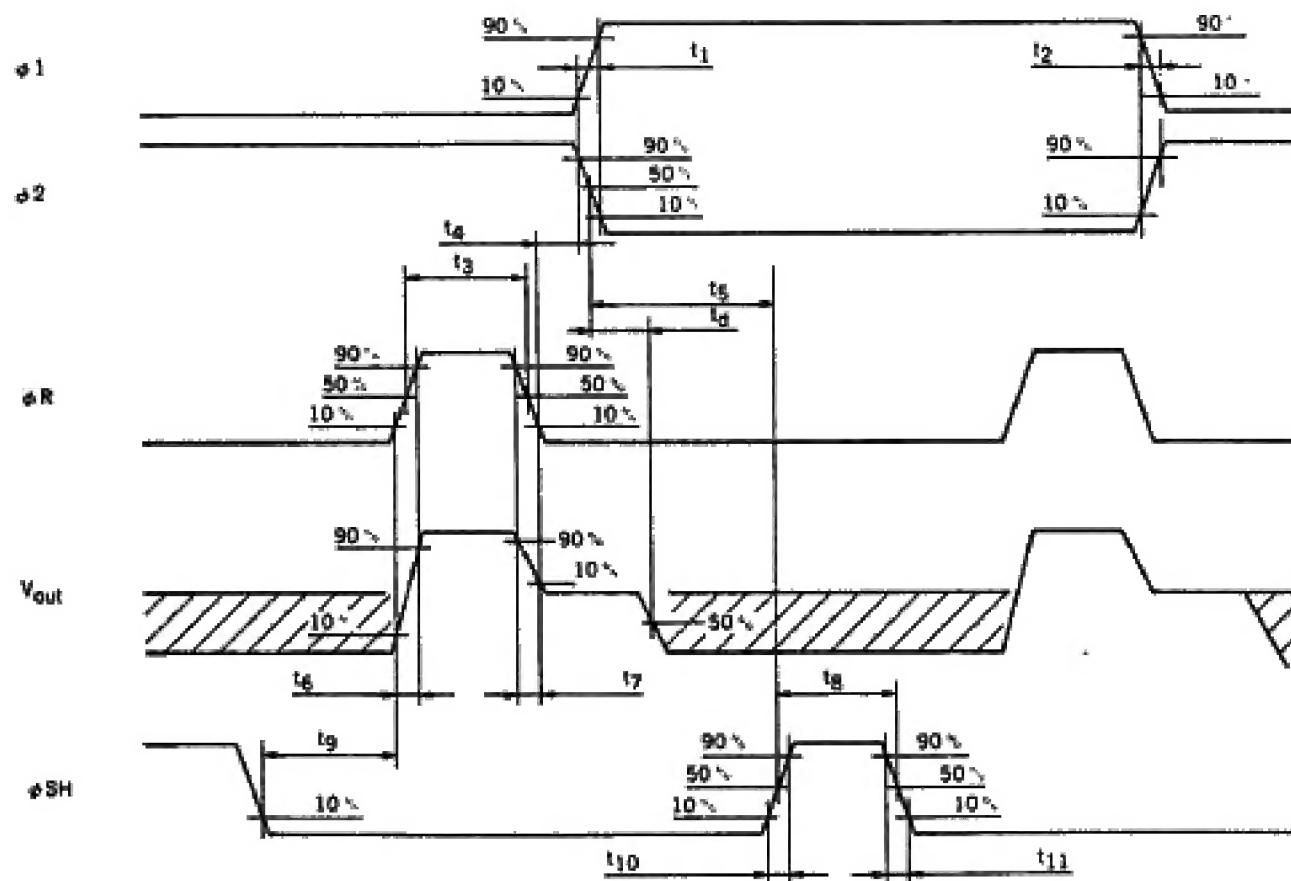
ITEM	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Saturation voltage	V_{sat}	1.4	2.0		V	
Saturation exposure	SE		0.3		Lxs	White fluorescent lamp
Photo response non-uniformity	PRNU		± 5	± 10	%	V_{out} : 500 mV, white fluorescent lamp
Average dark signal	ADS		1	5	mV	Optical input interruption
Dark signal non-uniformity	DSNU		3	10	mV	Optical input interruption, peak value
Power consumption	P_w		50	100	mW	
Output impedance	Z_o	0.3	0.6	1	k Ω	
Response	R	12.5	18.0	23.4	V/Lxs	W lamp
	R	4.2	6.0	7.8	V/Lsx	White fluorescent lamp
Response peak wavelength			550		nm	
Offset level	V_{OS}	4.5	6.5	8.5	V	
Input capacity of shift register clock pin	$C_{\phi 1}$		700	1000	pF	
	$C_{\phi 2}$					
Reset pin input capacity	$C_{\phi R}$		5	15	pF	
Input capacity of sample and hold pin	$C_{\phi SH}$		5	15	pF	
Input capacity of transfer gate signal pin	$C_{\phi TG}$		50	150	pF	
Output rise delay time	t_d		20	50	ns	

T-41-55

TIMING CHART

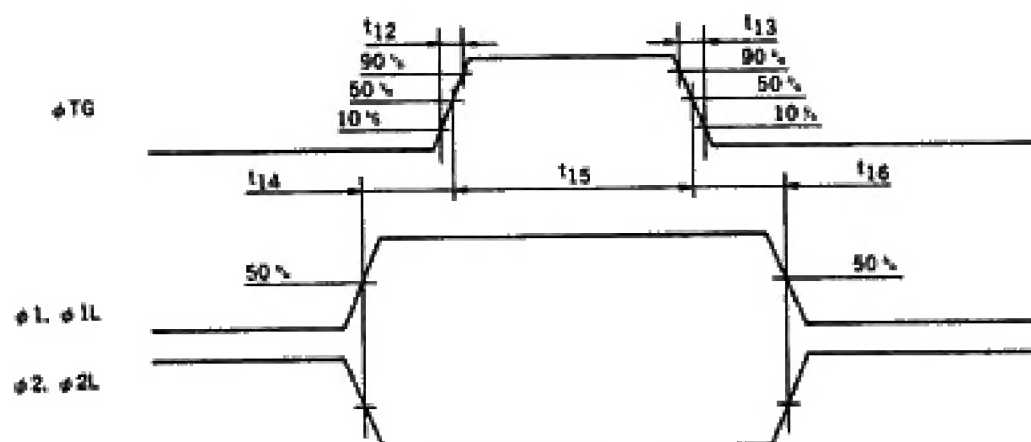


Note: V_{out} = Output when SH not used
 $V_{out}(SH)$ = Output when SH used

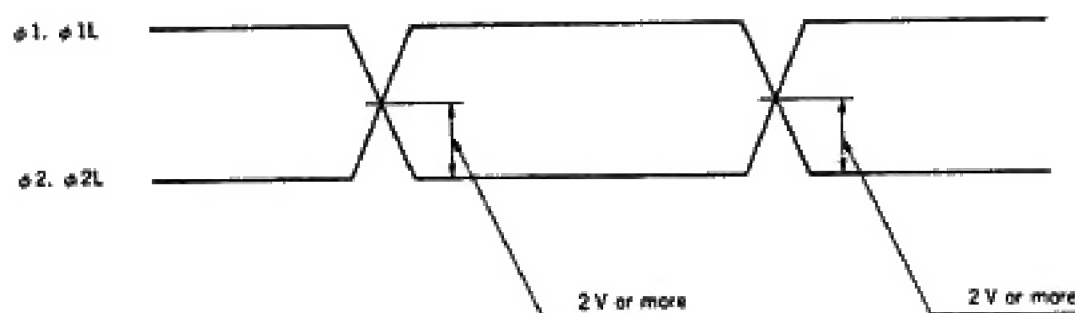
Timing chart for $\phi 1$, $\phi 2$, ϕR , ϕSH , and V_{out} 

Timing chart for ϕTG , $\phi 1$, $\phi 1L$, $\phi 2$, $\phi 2L$

T-41-55



Cross points $\phi 1$, $\phi 1L$, $\phi 2$, $\phi 2L$



Name	MIN.	TYP.	MAX.
$t_{1,12}$	0	50	150
t_3	20	250	
t_4	0	20	500
t_5	100	200	500
t_6, t_7	0	20	50
t_8	50	100	
t_9	0	20	
t_{10}, t_{11}	0	20	100
t_{12}, t_{13}	0	50	100
t_{14}, t_{16}	10	100	
t_{15}	300	1000	

(ns)

DEFINITIONS OF CHARACTERISTIC ITEMS

T-41-55

1. Saturation voltage: V_{sat}

The point at which the response linearity is lost.

2. Saturation exposure: SE

Product of intensity of illumination (lx) and storage time (s) when saturation of output voltage occurs

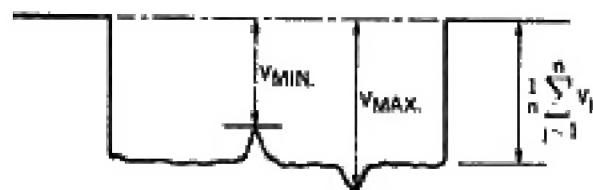
3. Photo response non-uniformity: PRNU

Expressed by the following expressing with the peak/bottom ratio to the average output voltage of all the valid bits.

$$PRNU(\%) = \left(\frac{V_{MAX. \text{ or } V_{MIN.}}}{\frac{1}{n} \sum_{j=1}^n V_j} - 1 \right) \times 100$$

n : Number of valid bits

V_j : Output voltage of each bit



4. Average dark signal: ADS

Output average voltage in light shielding

$$ADS(mV) = \frac{1}{n} \sum_{j=1}^n V_j$$

5. Dark signal non-uniformity: DSNU

Peak output voltage to the idle level in light shielding



6. Output impedance: Z_o

Output pin impedance when viewed externally

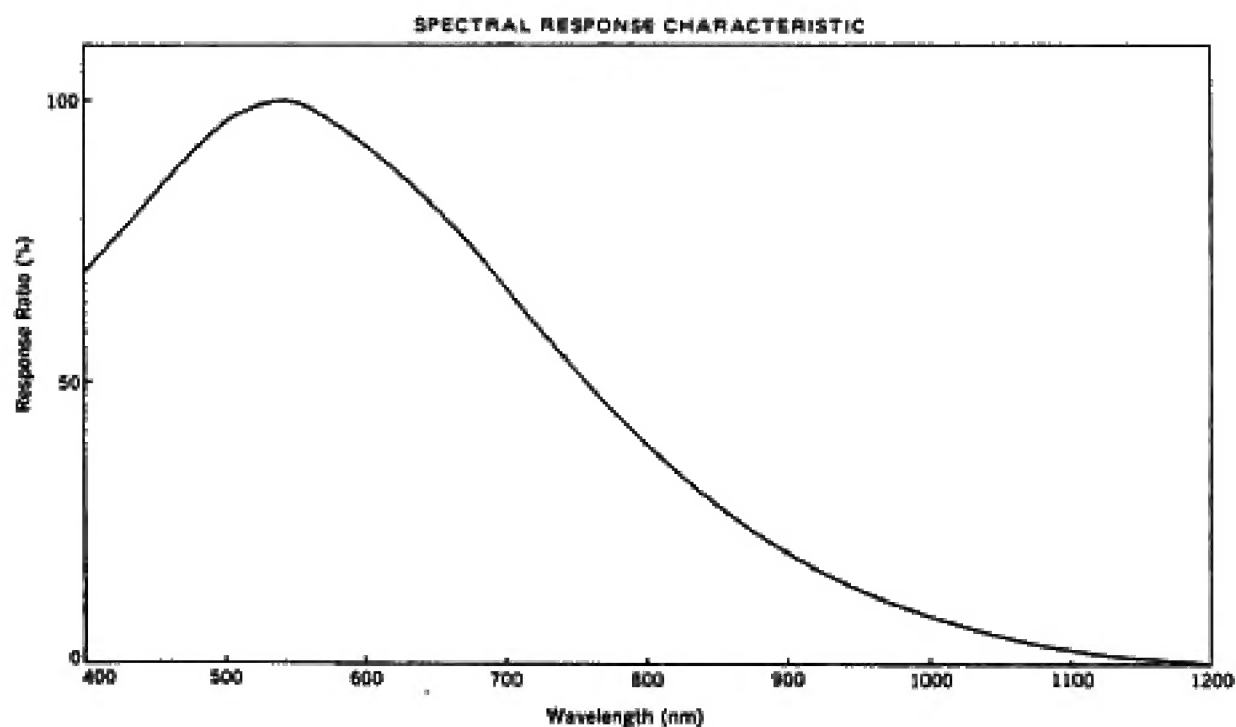
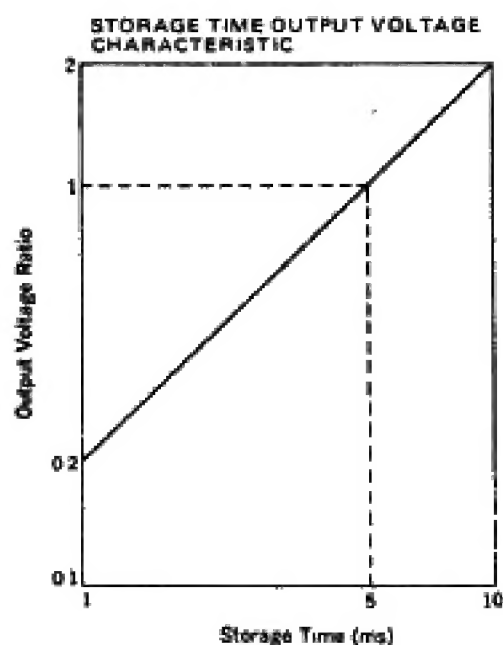
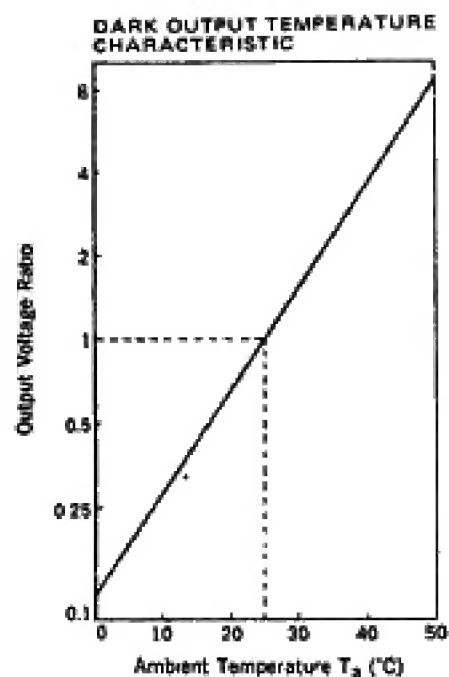
7. Response: R

Output voltage divided by exposure (lx-s).

Note that the response varies with the light source.

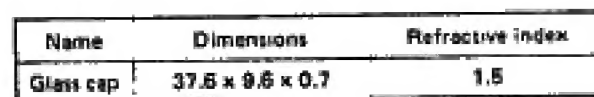
JARD CHARACTERISTIC CURVES ($T_a = 25^\circ\text{C}$)

T-41-55





PACKAGE DIMENSIONS (Unit: mm)



9